Electrical Specifications (T_A=+25℃)

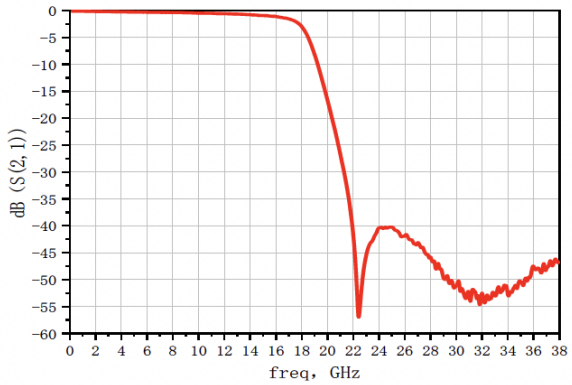
Parameter	Min.	Typ.	Max.	Unit
Cut-off Freq. (f_0)	-	16	-	GHz
Insertion Loss @ f_0	-	-	1.2	dB
Return Loss	21	-	-	dB
Out of band Attenuation	≥20@20.4GHz			dB
	≥40@22GHz			dB

Max. Input Power: 30dBm

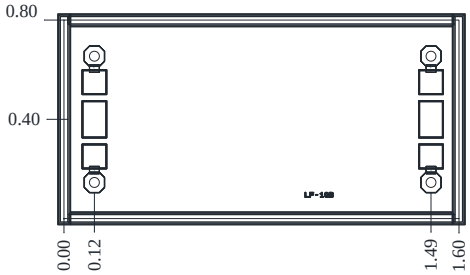
Operating Temperature: -55℃~+125℃

Storage Temperature: -65℃~+150℃

Typical Wideband Insertion Loss at T_A=25



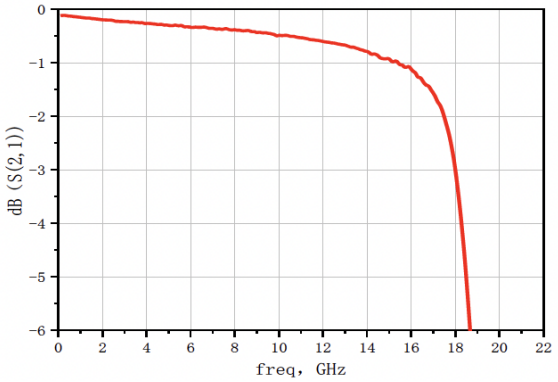
Outline Drawing



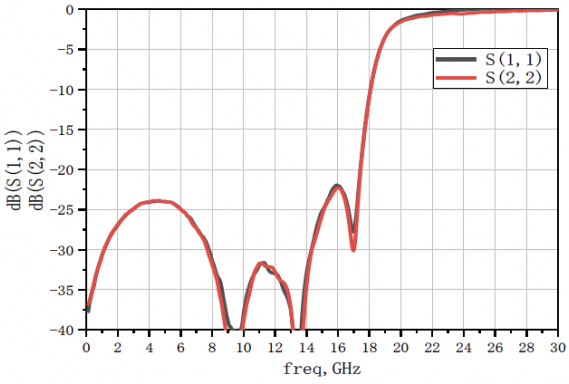
Notes:

1. Dimensions are in millimeters. Tolerance: ±0.05 mm
2. Die thickness is 0.1 mm
3. Typical bond pad size is 0.1 x 0.1 mm

Typical Insertion Loss at T_A=25



Typical Return Loss at T_A=25



Recommended Assembly Diagram

Notes:

1. Die is back-metallized and can be mounted with AuSn eutectic preform or with electrically conductive epoxy.
2. We recommend using Φ 25um Au wire for wire-bonding, with max wire length of 400um.
3. Sinter using AuSn (80/20) alloy, ensuring the temperature does not exceed 300°C for a maximum of 30 seconds.
4. Handle die in clean environment. Do not attempt to clean the chip using liquid cleaning systems.
5. Die is ESD sensitive. ESD protection is required during usage and storage.